

TrenchMOS™ transistor

Standard level FET

BUK7618-55

GENERAL DESCRIPTION

N-channel enhancement mode standard level field-effect power transistor in a plastic envelope suitable for surface mounting. Using 'trench' technology the device features very low on-state resistance and has integral zener diodes giving ESD protection up to 2kV. It is intended for use in automotive and general purpose switching applications.

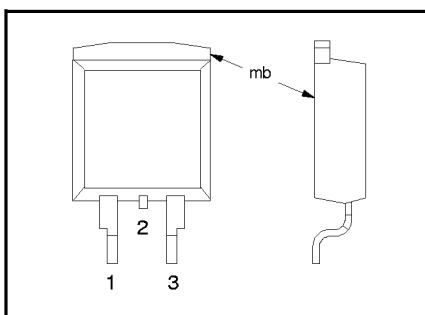
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	55	V
I_D	Drain current (DC)	57	A
P_{tot}	Total power dissipation	125	W
T_j	Junction temperature	175	°C
$R_{DS(ON)}$	Drain-source on-state resistance $V_{GS} = 10\text{ V}$	18	mΩ

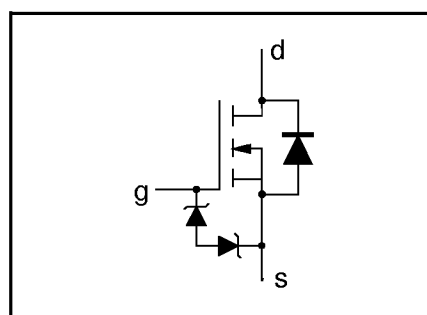
PINNING - SOT404

PIN	DESCRIPTION
1	gate
2	drain
3	source
mb	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	55	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	55	V
$\pm V_{GS}$	Gate-source voltage	-	-	16	V
I_D	Drain current (DC)	$T_{mb} = 25\text{ °C}$	-	57	A
I_D	Drain current (DC)	$T_{mb} = 100\text{ °C}$	-	40	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25\text{ °C}$	-	228	A
P_{tot}	Total power dissipation	$T_{mb} = 25\text{ °C}$	-	125	W
T_{stg}, T_j	Storage & operating temperature	-	- 55	175	°C

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage, all pins	Human body model (100 pF, 1.5 kΩ)	-	2	kV

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	-	-	1.2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	Minimum footprint, FR4 board	50	-	K/W

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STATIC CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}; T_j = -55^\circ\text{C}$	55	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\text{ mA}; T_j = -55^\circ\text{C}$	50	-	-	V
		$T_j = 175^\circ\text{C}$	2.0	3.0	4.0	V
		$T_j = -55^\circ\text{C}$	1.0	-	-	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 55\text{ V}; V_{GS} = 0\text{ V}; T_j = 175^\circ\text{C}$	-	-	4.4	V
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 10\text{ V}; V_{DS} = 0\text{ V}; T_j = 175^\circ\text{C}$	-	0.05	10	μA
		$T_j = 175^\circ\text{C}$	-	-	500	μA
$\pm V_{(BR)GSS}$	Gate-source breakdown voltage	$I_G = \pm 1\text{ mA}; T_j = 175^\circ\text{C}$	-	0.02	1	μA
			-	-	20	μA
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 175^\circ\text{C}$	16	-	-	V
			-	15	18	$\text{m}\Omega$
			-	-	38	$\text{m}\Omega$

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25\text{ V}; I_D = 25\text{ A}$	6	30	-	S
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	1500	2000	pF
C_{oss}	Output capacitance		-	370	470	pF
C_{rss}	Feedback capacitance		-	170	250	pF
$t_{d\text{ on}}$	Turn-on delay time	$V_{DD} = 30\text{ V}; I_D = 25\text{ A}; V_{GS} = 10\text{ V}; R_G = 10\ \Omega$	-	15	22	ns
t_r	Turn-on rise time		-	30	60	ns
$t_{d\text{ off}}$	Turn-off delay time	Resistive load	-	35	50	ns
t_f	Turn-off fall time		-	25	38	ns
L_d	Internal drain inductance	Measured from upper edge of drain tab to centre of die	-	2.5	-	nH
L_s	Internal source inductance	Measured from source lead soldering point to source bond pad	-	7.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

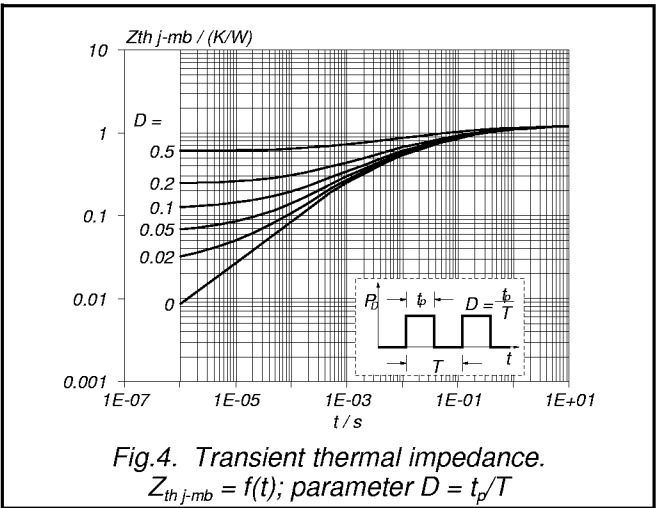
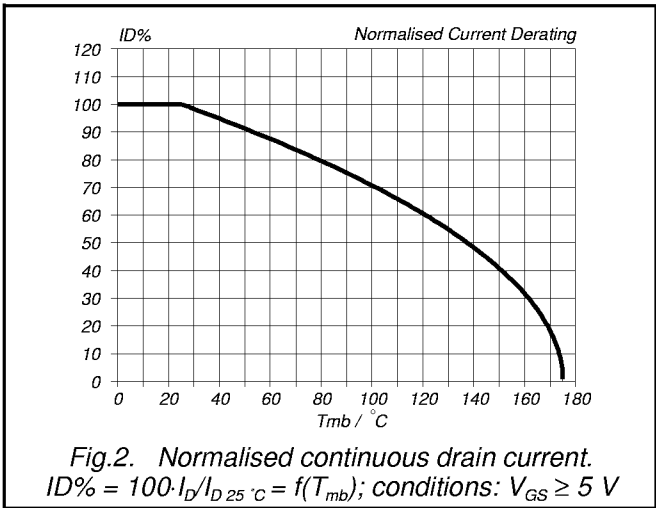
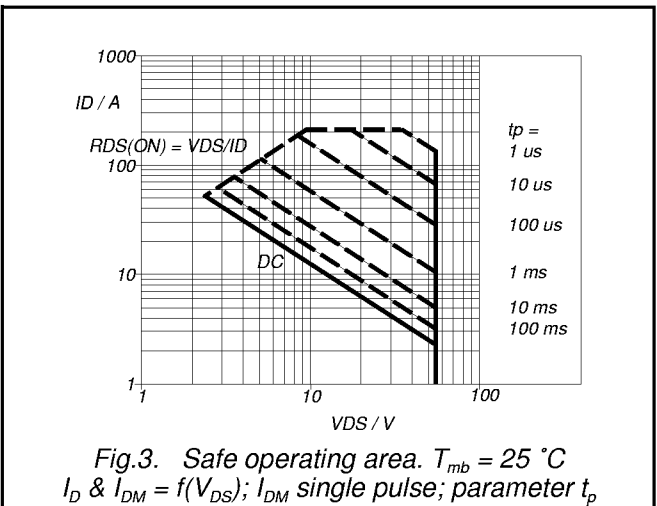
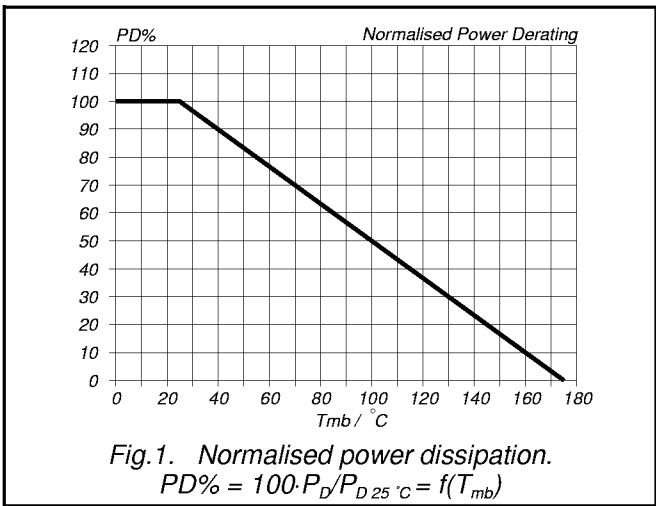
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current		-	-	57	A
I_{DRM}	Pulsed reverse drain current		-	-	200	A
V_{SD}	Diode forward voltage	$I_F = 25\text{ A}; V_{GS} = 0\text{ V}$	-	0.95	1.2	V
		$I_F = 50\text{ A}; V_{GS} = 0\text{ V}$	-	1.0	-	V
t_{rr}	Reverse recovery time	$I_F = 50\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_{GS} = -10\text{ V}; V_R = 30\text{ V}$	-	48	-	ns
Q_{rr}	Reverse recovery charge		-	0.1	-	μC

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AVALANCHE LIMITING VALUE

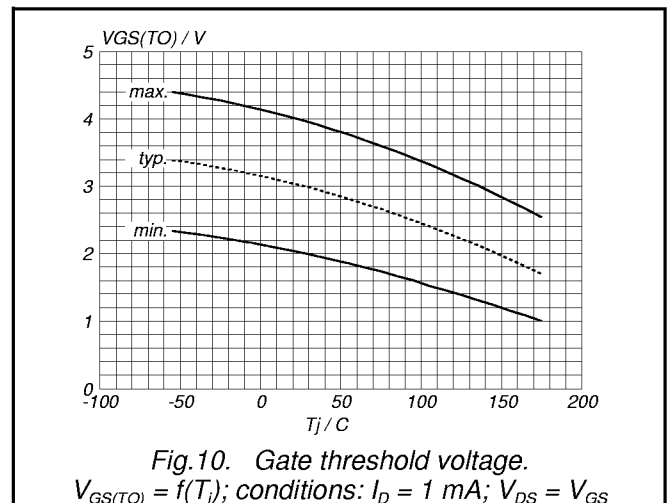
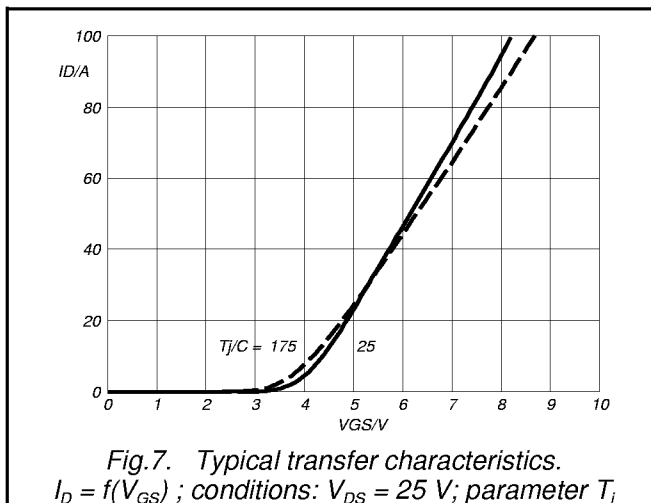
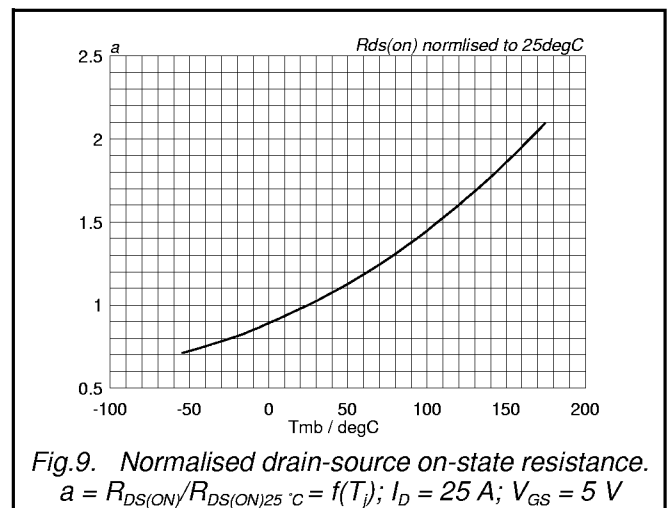
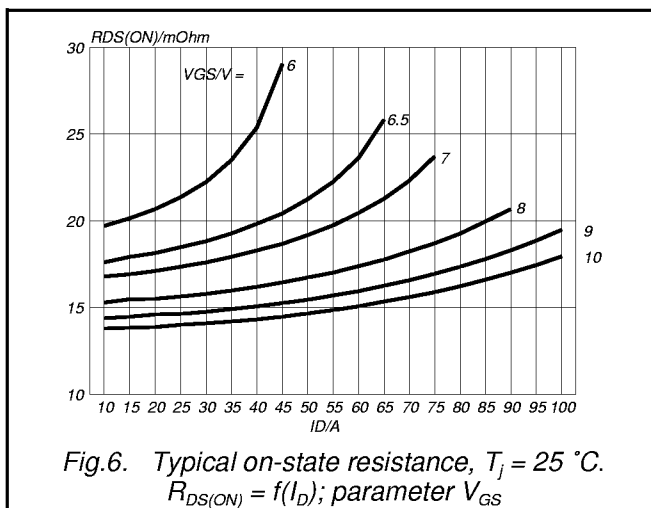
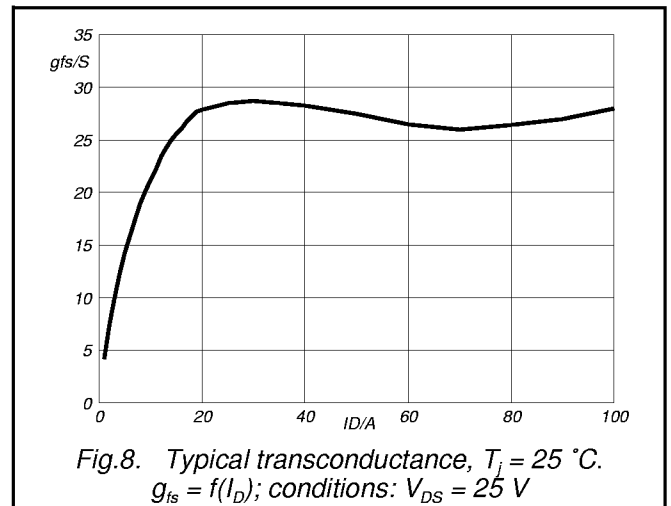
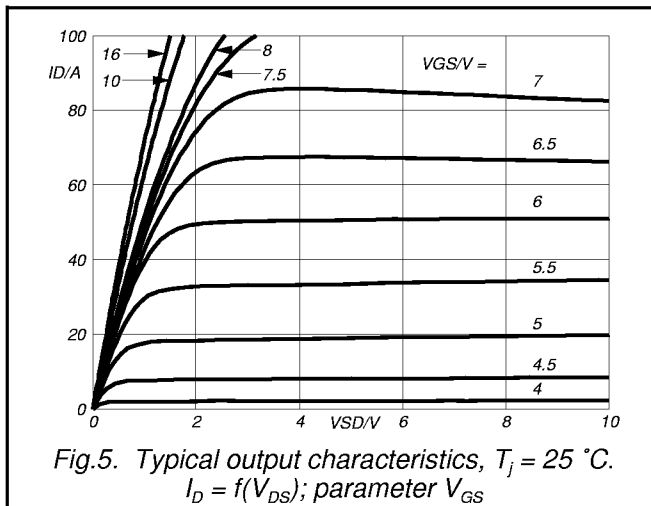
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 50\text{ A}$; $V_{DD} \leq 25\text{ V}$; $V_{GS} = 10\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $T_{mb} = 25\text{ }^\circ\text{C}$	-	-	125	mJ



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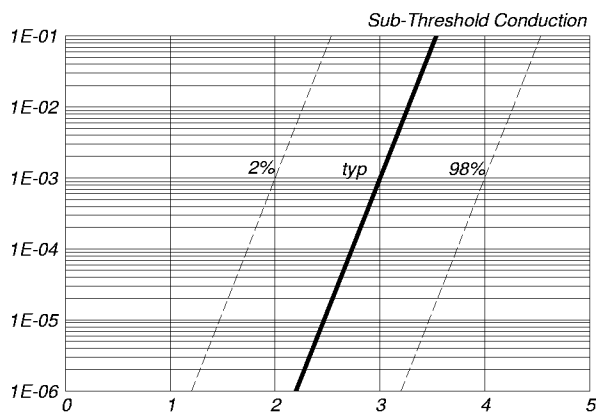


Fig. 11. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25^\circ\text{C}$; $V_{DS} = V_{GS}$

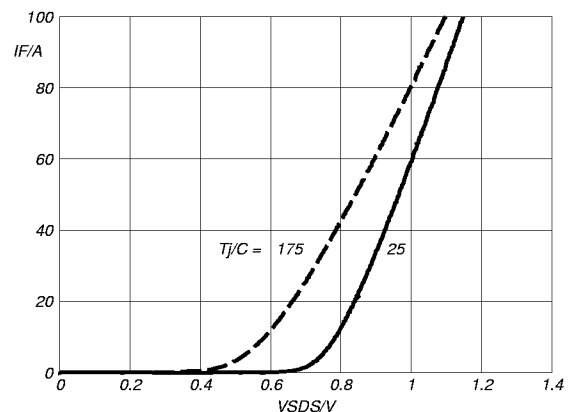


Fig. 14. Typical reverse diode current.
 $I_F = f(V_{DS})$; conditions: $V_{GS} = 0\text{ V}$; parameter T_j

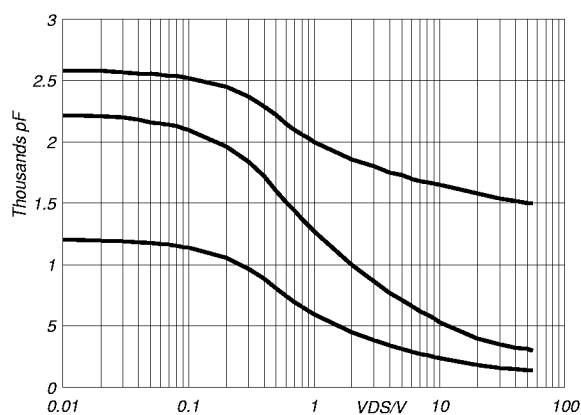


Fig. 12. Typical capacitances, C_{iss} , C_{oss} , C_{rss} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0\text{ V}$; $f = 1\text{ MHz}$

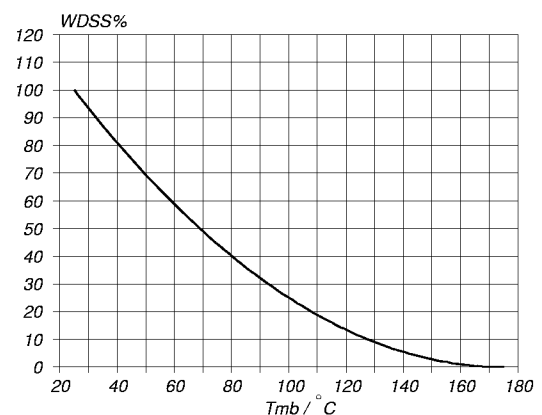


Fig. 15. Normalised avalanche energy rating.
 $W_{DSS}\% = f(T_{mj})$; conditions: $I_D = 75\text{ A}$

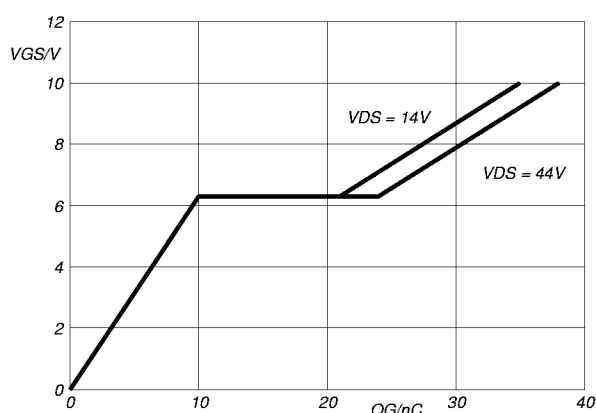


Fig. 13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 50\text{ A}$; parameter V_{DS}

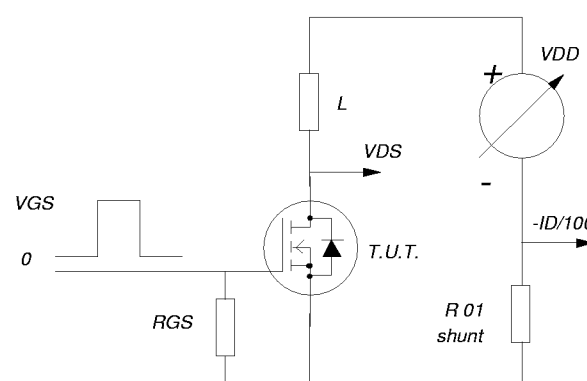
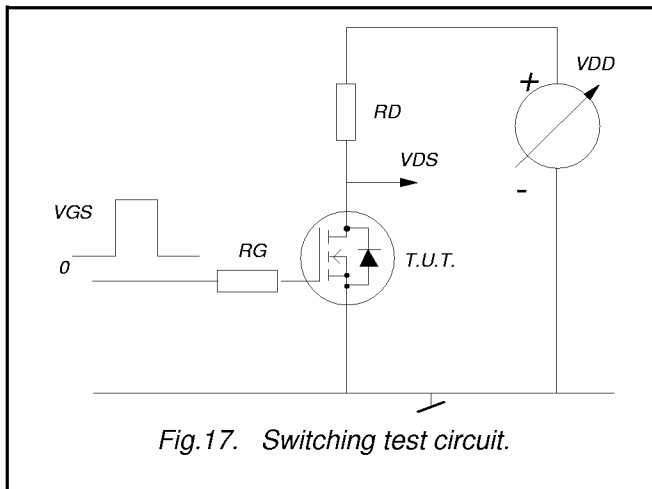


Fig. 16. Avalanche energy test circuit.
 $W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS} / (BV_{DSS} - V_{DD})$

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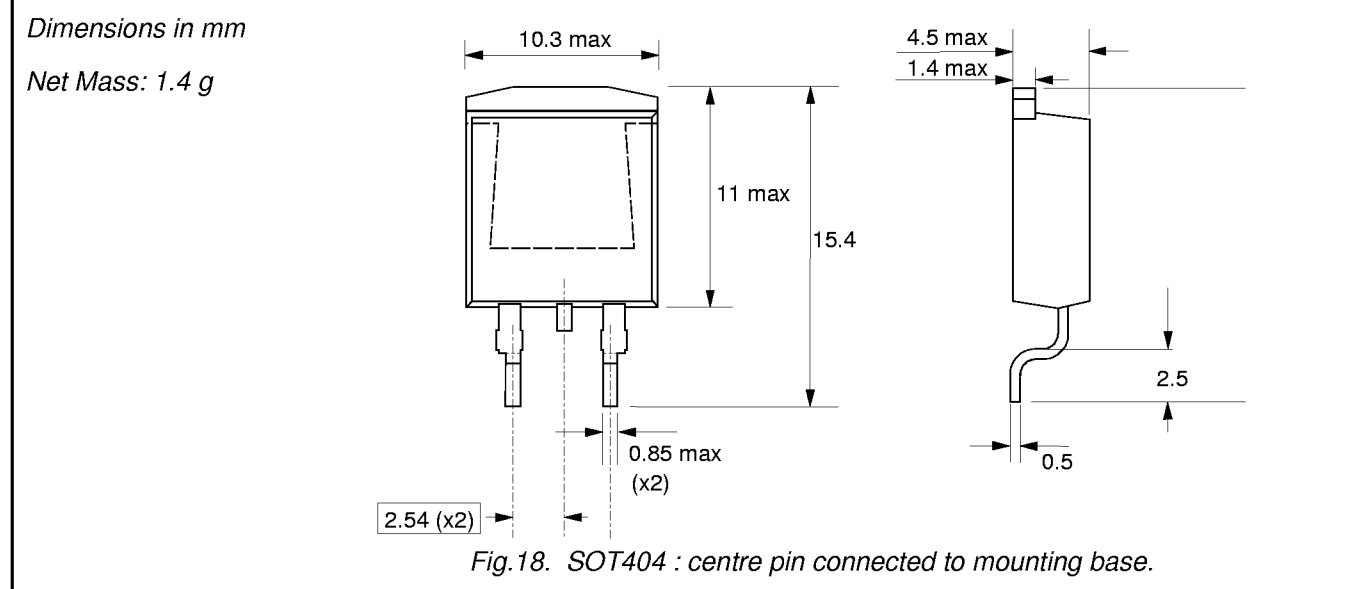


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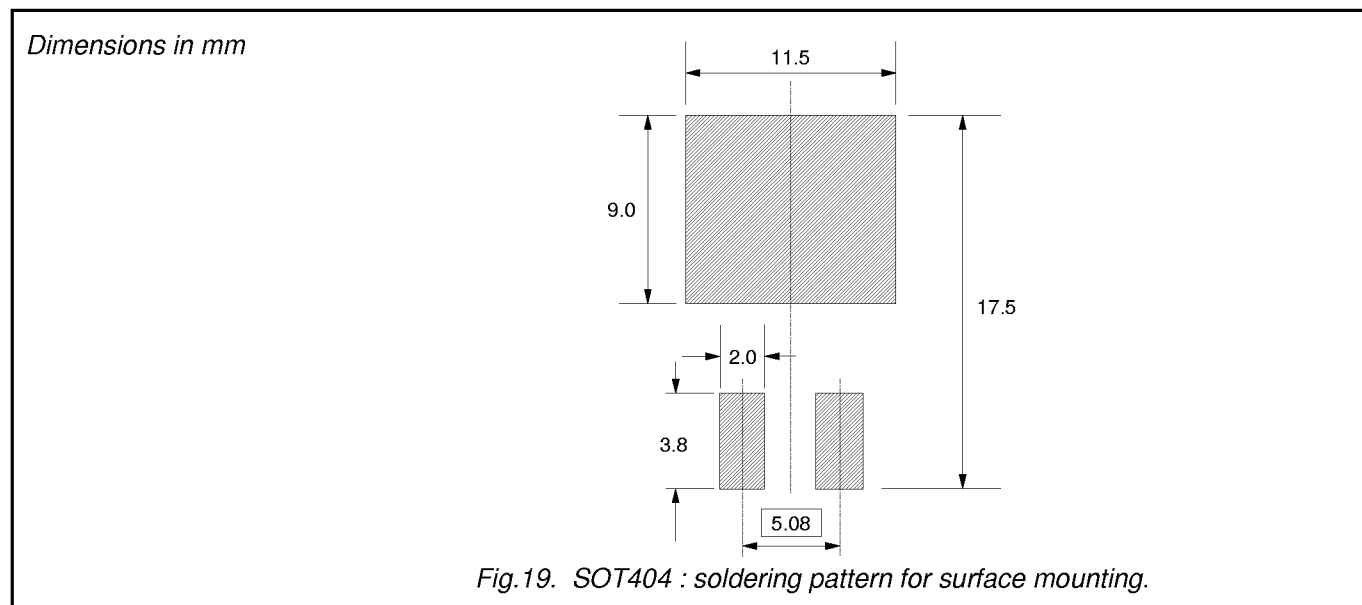
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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".